

Silicon NPN Power Transistor

KSD5062

DESCRIPTION

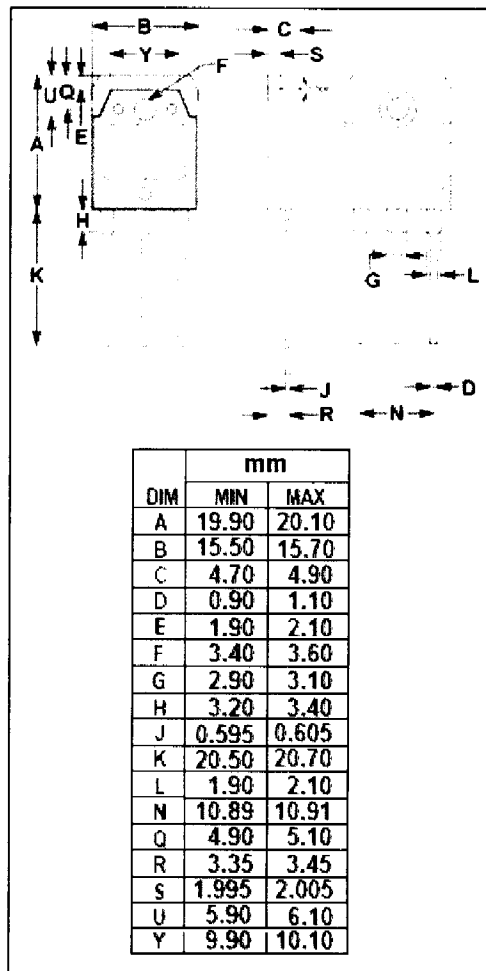
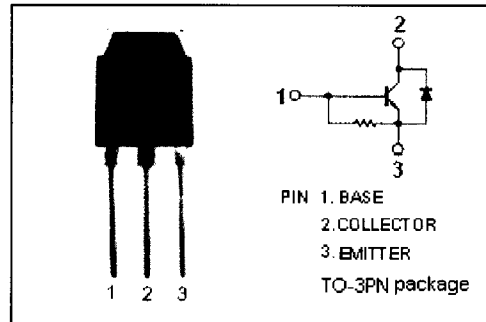
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

APPLICATIONS

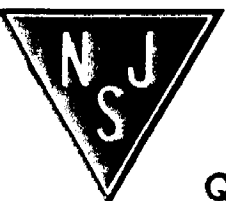
- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
I_{CP}	Collector Current-Peak	16	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	120	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 4A; I_B= 0.8A$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 4A; I_B= 0.8A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 800V; I_E= 0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 4V; I_C= 0$	40		200	mA
h_{FE}	DC Current Gain	$I_C= 1A; V_{CE}= 5V$	8			
f_T	Current-Gain—Bandwidth Product	$I_C= 1A; V_{CE}= 10V$		3		MHz
V_{ECF}	C-E Diode Forward Voltage	$I_F= 5A$			2.0	V
t_f	Fall Time	$I_C= 4A, I_{B1}= 0.8A; I_{B2}= -1.6A$ $R_L= 50\ \Omega; V_{CC}= 200V$			0.4	μs